



**General Description:**

- (1) Chip Dimension  
 Chip Size= 10 mil x 23 mil (270um x 595um)  
 Chip Thickness= 100±10µm  
 Bonding Pad= 70±5µm
- (2) Electrode:  
 P (Anode) → Au  
 N (Cathode) → Au
- (3) Structure:  
 Refer to drawing  
 SiO<sub>2</sub> Passivated surface

**Electro-optical Characteristics**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage	V <sub>F</sub>	2.9	3.2	3.6	V	I <sub>F</sub> =20mA
Dominant Wavelength	λ <sub>D</sub>	447.5	-	465	nm	I <sub>F</sub> =20mA
Reverse Current	I <sub>R</sub>	0	-	1	µA	V <sub>R</sub> =-5V

Luminous Intensity( I <sub>v</sub> ) mcd at I <sub>F</sub> =20mA	Dominant Wavelength(nm)							
	Range	447.5~450	450~452.5	452.5~455	455~457.5	457.5~460	460~462.5	462.5~465
80~90	*							
90~100	*	*	*					
100~120	*	*	*	*	*			
120~140		*	*	*	*	*		
140~160		*	*	*	*	*	*	*
160~180				*	*	*	*	*
180~200					*	*	*	*
200~220						*	*	*
220~240								*
240~260								*

**Features:**

- 1. High Luminous Intensity
- 2. Sideview SMD Applications
- 3. Long Operation Life
- 4. 100% probing Test

**Notes:**

- 1. Dominant wavelength includes an error of ± 1nm
- 2. Luminous intensity includes an error of ±10%
- 3. Luminous intensity is measured on bare chip
- 4. InGaN LED is sensitive to ESD